

1N5550 1N5553
1N5551 1N5554
1N5552

**GLASS PASSIVATED
SILICON RECTIFIERS
3.0 AMP, 200 THRU 1000 VOLT**



GPR-4AM CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 1N5550 series types are silicon rectifiers mounted in a hermetically sealed, glass passivated package designed for general purpose applications where high reliability is required.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

	SYMBOL	1N5550	1N5551	1N5552	1N5553	1N5554	UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	200	400	600	800	1000	V
DC Blocking Voltage	V_R	200	400	600	800	1000	V
RMS Reverse Voltage	$V_{R(RMS)}$	140	280	420	560	700	V
Average Forward Current ($T_A=55^\circ\text{C}$)	I_O			3.0			A
Peak Forward Surge Current, $t_p=8.3\text{ms}$	I_{FSM}			100			A
Operating and Storage Junction Temperature	T_J, T_{stg}			-65 to +200			$^\circ\text{C}$
Thermal Resistance (Note 1)	θ_{JL}			30			$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_R	$V_R=\text{Rated } V_{RRM}$		1.0	μA
I_R	$V_R=\text{Rated } V_{RRM}, T_A=100^\circ\text{C}$		75	μA
V_F	$I_F=3.0\text{A}$ (200V thru 600V)		1.0	V
V_F	$I_F=3.0\text{A}$ (800V thru 1000V)		1.1	V
BV_R	$I_R=50\mu\text{A}$ (1N5550)	240		V
BV_R	$I_R=50\mu\text{A}$ (1N5551)	460		V
BV_R	$I_R=50\mu\text{A}$ (1N5552)	660		V
BV_R	$I_R=50\mu\text{A}$ (1N5553)	880		V
BV_R	$I_R=50\mu\text{A}$ (1N5554)	1100		V
t_{rr}	$I_F=0.5\text{A}, I_R=1.0\text{A}, I_{rr}=0.25\text{A}$ (200V thru 600V)		2.0	μs
t_{rr}	$I_F=0.5\text{A}, I_R=1.0\text{A}, I_{rr}=0.25\text{A}$ (800V thru 1000V)		4.0	μs

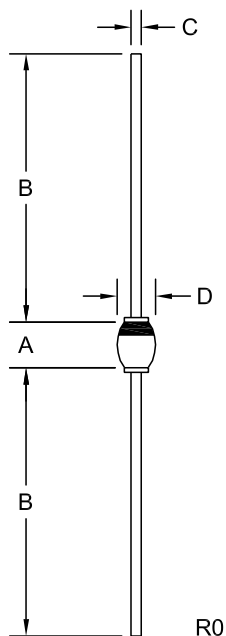
Notes: (1) At 0.375 inch (9.52mm) lead length from body.

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GPR-4AM CASE - MECHANICAL OUTLINE



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.165	0.189	4.20	4.80
B	1.024	—	26.00	—
C	0.037	0.042	0.95	1.06
D	0.130	0.175	3.30	4.45

GPR-4AM (REV: R0)

R2 (27-February 2013)